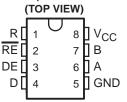
- Integrated Transient Voltage Suppression
- ESD Protection for Bus Terminals Exceeds:
   ±30 kV IEC 61000-4-2, Contact Discharge
   ±15 kV IEC 61000-4-2, Air-Gap Discharge
   ±15 kV EIA/JEDEC Human Body Model
- Circuit Damage Protection of 400-W Peak (Typical) Per IEC 61000-4-5
- Controlled Driver Output-Voltage Slew Rates Allow Longer Cable Stub Lengths
- 250-kbps in Electrically Noisy Environments
- Open-Circuit Fail-Safe Receiver Design
- 1/4 Unit Load Allows for 128 Devices Connected on Bus
- Thermal Shutdown Protection
- Power-Up/-Down Glitch Protection
- Each Transceiver Meets or Exceeds the Requirements of TIA/EIA-485 (RS-485) and ISO/IEC 8482:1993(E) Standards
- Low Disabled Supply Current 300 μA Max
- Pin Compatible With SN75176
- Applications:
  - Industrial Networks
  - Utility Meters
  - Motor Control

### description

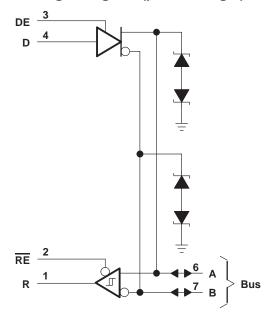
The SN75LBC184 and SN65LBC184 are differential data line transceivers in the trade-standard footprint of the SN75176 with built-in protection against high-energy noise transients. This feature provides a substantial increase in reliability for better immunity to noise transients coupled to the data cable over most existing devices. Use of these circuits provides a reliable low-cost direct-coupled (with no isolation transformer) data line interface without requiring any external components.

The SN75LBC184 and SN65LBC184 can withstand overvoltage transients of 400-W peak (typical). The conventional combination wave called out in IEC 61000-4-5 simulates the overvoltage transient and models a unidirectional surge caused by overvoltages from switching and secondary lightning transients.

SN65LBC184D (Marked as 6LB184) SN75LBC184D (Marked as 7LB184) SN65LBC184P (Marked as 65LBC184) SN75LBC184P (Marked as 75LBC184)



# functional logic diagram (positive logic)



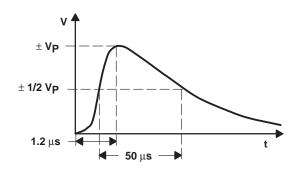


Figure 1. Surge Waveform — Combination Wave



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



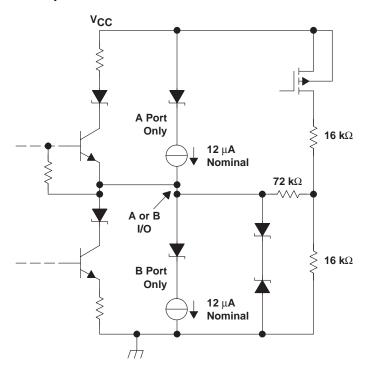
# description (continued)

A biexponential function defined by separate rise and fall times for voltage and current simulates the combination wave. The standard 1.2  $\mu$ s/50  $\mu$ s combination waveform is shown in Figure 1 and in the test description in Figure 15.

The device also includes additional desirable features for party-line data buses in electrically noisy environment applications including industrial process control. The differential-driver design incorporates slew-rate-controlled outputs sufficient to transmit data up to 250 kbps. Slew-rate control allows longer unterminated cable runs and longer stub lengths from the main backbone than possible with uncontrolled and faster voltage transitions. A unique receiver design provides a fail-safe output of a high level when the inputs are left floating (open circuit). The SN75LBC184 and SN65LBC184 receiver also includes a high input resistance equivalent to one-fourth unit load allowing connection of up to 128 similar devices on the bus.

The SN75LBC184 is characterized for operation from 0°C to 70°C. The SN65LBC184 is characterized from –40°C to 85°C.

# schematic of inputs and outputs





### DRIVER FUNCTION TABLE

INPUT	ENABLE	OUTPUTS		
D	DE	Α	В	
Н	Н	Н	L	
L	Н	L	Н	
Х	L	Z	Z	

H = high level, L = low level, ? = indeterminate, X = irrelevant, Z = high impedance (off)

### **RECEIVER FUNCTION TABLE**

DIFFERENTIAL INPUTS	ENABLE	OUTPUT
A – B	RE	R
V <sub>ID</sub> ≥ 0.2 V	L	Н
$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$	L	?
V <sub>ID</sub> ≤ -0.2 V	L	L
X	Н	Z
Open	L	Н

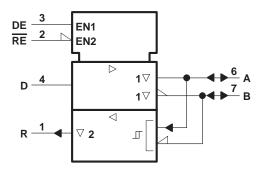
H = high level, L = low level, ? = indeterminate, X = irrelevant, Z = high impedance (off)

### **AVAILABLE OPTIONS**

	PACKAGE					
TA	PLASTIC SMALL-OUTLINE <sup>†</sup> (JEDEC MS-012)	PLASTIC DUAL-IN-LINE PACKAGE (JEDEC MS-001)				
0°C to 70°C	SN75LBC184D	SN75LBC184P				
-40°C to 85°C	SN65LBC184D	SN65LBC184P				

<sup>†</sup> Add R suffix for taped and reel.

# logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



# SN65LBC184, SN75LBC184 DIFFERENTIAL TRANSCEIVER WITH TRANSIENT VOLTAGE SUPPRESSION

SLLS236G - OCTOBER 1996 - REVISED FEBRUARY 2009

# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC</sub> (see Note 1)		0.5 V to 7 V
Continuous voltage range at any bus terminal		–15 V to 15 V
Data input/output voltage		0.3 V to 7 V
Receiver output current, IO		±20 mA
Electrostatic discharge: Contact discharge (IEC61000-4-2	2) A, B, GND (see Note 2)	±30 kV
Air discharge (IEC61000-4-2)	A, B, GND (see Note 2)	±15 kV
Human body model (see Note 3)	A, B, GND (see Note 2)	±15 kV
	All pins	±3 kV
All terminals (Class 3A) (see Note	e 2)	±8 kV
All terminals (Class 3B) (see Note	ə 2)	±200 V
Electrical Fast Transient/Burst (IEC 61000-4-4)	A, B, GND	±4 kV
Continuous total power dissipation (see Note 4)		Internally Limited

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential input/output bus voltage, are with respect to network ground terminal.
  - 2. GND and bus terminal ESD protection is beyond readily available test equipment capabilities for IEC 61000-4-2, EIA/JEDEC test method A114-A and MIL-STD-883C method 3015. Ratings listed are limits of test equipment; device performance exceeds these
  - 3. Tested in accordance with JEDEC Standard 22, Test Method A114-A and IEC 60749-26.
  - 4. The driver shuts down at a junction temperature of approximately 160°C. To operate below this temperature, see the Dissipation Rating Table.

### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR T <sub>A</sub> = 70°C ABOVE T <sub>A</sub> = 25°C POWER RATING		T <sub>A</sub> = 85°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW
Р	1150 mW	9.2 mW/°C	736 mW	598 mW

### recommended operating conditions

		MIN‡	TYP	MAX	UNIT
Supply voltage, V <sub>CC</sub>		4.75	5	5.25	V
Voltage at any bus terminal (separatel	y or common mode), V <sub>I</sub> or V <sub>I</sub> C	-7		12	V
High-level input voltage, V <sub>IH</sub>	D, DE, and RE	2			V
Low-level input voltage, V <sub>IL</sub>	D, DE, and RE			8.0	V
Differential input voltage,  VID				12	V
	Driver	-60			mA
High-level output current, IOH	Receiver	-8			mA
	Driver			60	
Low-level output current, IOL	Receiver			4	mA
On another from all temperature T	SN75LBC184	0		70	°C
Operating free-air temperature, T <sub>A</sub>	SN65LBC184	-40		85	°C

<sup>‡</sup> The algebraic convention, in which the less-positive (more-negative) limit is designated minimum, is used in this data sheet.



# **DRIVER SECTION**

# electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	ALTERNATE SYMBOLS	TEST CONDITIONS	MIN	түр†	MAX	UNIT
			$DE = \overline{RE} = 5 \text{ V}$ , No Load		12	25	mA
lcc	Supply current	NA	DE = 0 V, RE = 5 V, No Load		175	300	μΑ
lН	High-level input current (D, DE, RE)	NA	V <sub>I</sub> = 2.4 V			50	μΑ
I <sub>I</sub> L	Low-level input current (D, DE, RE)	NA	V <sub>I</sub> = 0.4 V	-50			μΑ
			V <sub>O</sub> = -7 V	-250	-120		
los	Short-circuit output current (see Note 5)	NA	VO = VCC			250	mA
(See Note 3)			V <sub>O</sub> = 12 V			250	
loz	High-impedance output current	NA		See	Receive	er I <sub>I</sub>	mA
Vo	Output voltage	V <sub>oa</sub> , V <sub>ob</sub>	I <sub>O</sub> = 0	0		VCC	V
VOC(PP)	Peak-to-peak change in common- mode output voltage during state transitions	NA	See Figures 5 and 6		0.8		٧
Voc	Common-mode output voltage	V <sub>os</sub>	See Figure 4	1		3	V
ΔV <sub>OC</sub> (SS)	Magnitude of change, common- mode steady-state output voltage	$ V_{OS} - \overline{V}_{OS} $	See Figure 5			0.1	٧
11/2-1	Magnitude of differential output	.,,	IO = 0	1.5		6	V
IVODI	voltage  V <sub>A</sub> – V <sub>B</sub>	Vo	$R_L = 54 \Omega$ , See Figure 4	1.5			V
Δ V <sub>OD</sub>	Change in differential voltage mag- nitude between logic states	$  V_t  -  \overline{V}_t  $	R <sub>L</sub> = 54 Ω			0.1	V

<sup>&</sup>lt;sup>†</sup> All typical values are measured with  $T_A = 25$ °C and  $V_{CC} = 5$  V.

NOTE 5: This parameter is measured with only one output being driven at a time.

# switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
t <sub>d(DH)</sub>	Differential output delay time, low-to-high-level output					1.3	μs
t <sub>d(DL)</sub>	Differential-output delay time, high-to-low-level output					1.3	μs
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output	1			0.5	1.3	μs
tPHL	Propagation delay time, high-to-low-level output	$R_L = 54 \Omega$ , See Figure 5	$C_L = 50 pF$ ,		0.5	1.3	μs
tsk(p)	Pulse skew ( t <sub>d(DH)</sub> - t <sub>d(DL)</sub>  )	See rigure 3			75	150	ns
t <sub>r</sub>	Rise time, single ended			0.25		1.2	μs
t <sub>f</sub>	Fall time, single ended			0.25		1.2	μs
<sup>t</sup> PZH	Output enable time to high level	$R_L = 110 \Omega$ ,	See Figure 2			3.5	μs
tPZL	Output enable time to low level	$R_L = 110 \Omega$ ,	See Figure 3			3.5	μs
<sup>t</sup> PHZ	Output disable time from high level	$R_L = 110 \Omega$ ,	See Figure 2			2	μs
tPLZ	Output disable time from low level	$R_L = 110 \Omega$ ,	See Figure 3			2	μs

# **RECEIVER SECTION**

# electrical characteristics over recommended operating conditions (unless otherwise noted)

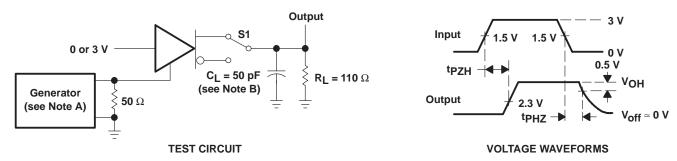
	PARAMETER	TEST C	TEST CONDITIONS			TYP <sup>†</sup>	MAX	UNIT
		$DE = \overline{RE} = 0 \text{ V},$	No Load				3.9	mA
ICC	Supply current (total package)	RE = 5 V, No Load	DE = 0 V,				300	μΑ
			V <sub>I</sub> = 12 V				250	
l			V <sub>I</sub> = 12 V,	$V_{CC} = 0$			250	
II.	Input current	Other input = 0 V	V <sub>I</sub> = -7 V		-200			μΑ
			$V_I = -7 V$ ,	VCC = 0	-200			
loz	High-impedance-state output current	$V_0 = 0.4 \text{ V to } 2.4 \text{ V}$					±100	μΑ
V <sub>hys</sub>	Input hysteresis voltage					70		mV
V <sub>IT+</sub>	Positive-going input threshold voltage						200	mV
V <sub>IT</sub> _	Negative-going input threshold voltage				-200			mV
Vон	High-level output voltage	I <sub>OH</sub> = -8 mA	Figure 7		2.8			V
VOL	Low-level output voltage	I <sub>OL</sub> = 4 mA	Figure 7	_			0.4	V

 $<sup>\</sup>dagger$  All typical values are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C.

# switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output		0			150	ns
tPHL	Propagation delay time, high-to-low-level output	$C_L = 50 \text{ pF},$	See Figure 7			150	ns
tsk(p)	Pulse skew ( tpHL - tpLH )					50	ns
t <sub>r</sub>	Rise time, single ended	0 5:			20		ns
t <sub>f</sub>	Fall time, single ended	See Figure 7			20		ns
<sup>t</sup> PZH	Output enable time to high level					100	ns
tPZL	Output enable time to low level	Coo Figure 8				100	ns
<sup>t</sup> PHZ	Output disable time from high level	See Figure 8				100	ns
tPLZ	Output disable time from low level					100	ns

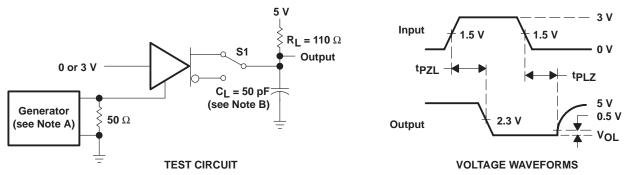
### PARAMETER MEASUREMENT INFORMATION



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle,  $t_f \le 10$  ns,  $t_f \le 10$  ns, t

B. C<sub>L</sub> includes probe and jig capacitance.

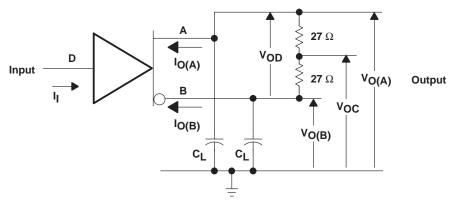
Figure 2. Driver tpzH and tpHZ Test Circuit and Voltage Waveforms



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle,  $t_f \le 10$  ns,  $t_f \le 10$  ns, t

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 3. Driver tpzL and tpLZ Test Circuit and Voltage Waveforms



NOTES: A. Resistance values are in ohms and are 1% tolerance.

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 4. Driver Test Circuit, Voltage, and Current Definitions



# PARAMETER MEASUREMENT INFORMATION

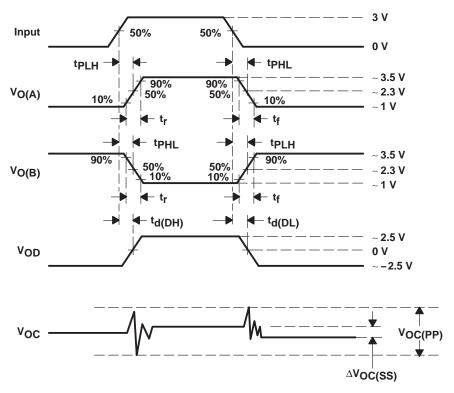
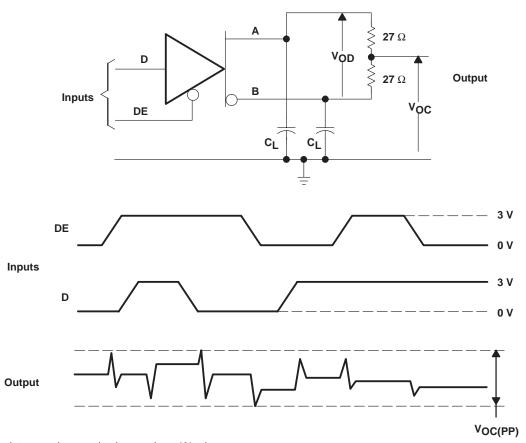


Figure 5. Driver Timing, Voltage and Current Waveforms



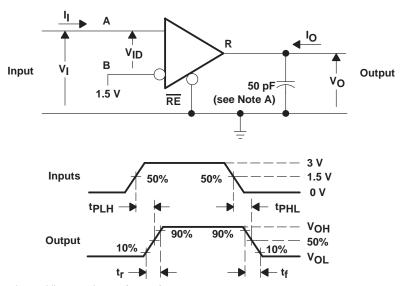
# PARAMETER MEASUREMENT INFORMATION



NOTES: A. Resistance values are in ohms and are 1% tolerance.

B. C<sub>L</sub> includes probe and jig capacitance (± 10%).

Figure 6. Driver V<sub>OC(PP)</sub> Test Circuit and Waveforms

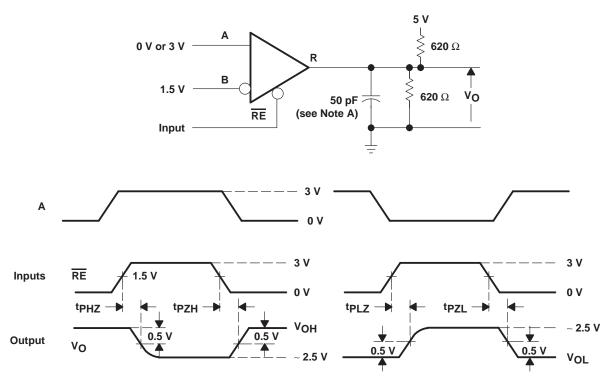


NOTE A: This value includes probe and jig capacitance ( $\pm$  10%).

Figure 7. Receiver  $t_{\mbox{\scriptsize PLH}}$  and  $t_{\mbox{\scriptsize PHL}}$  Test Circuit and Voltage Waveforms



# PARAMETER MEASUREMENT INFORMATION



NOTE A: This value includes probe and jig capacitance ( $\pm$  10%).

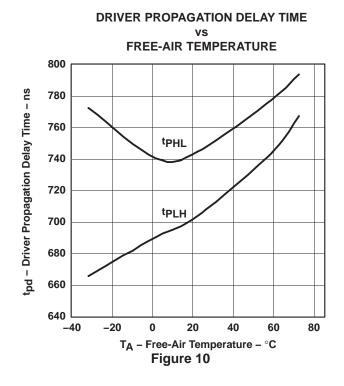
Figure 8. Receiver tpzl, tplz, tpzH, and tpHZ Test Circuit and Voltage Waveforms

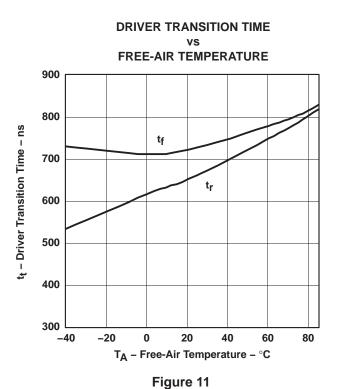
### **TYPICAL CHARACTERISTICS**

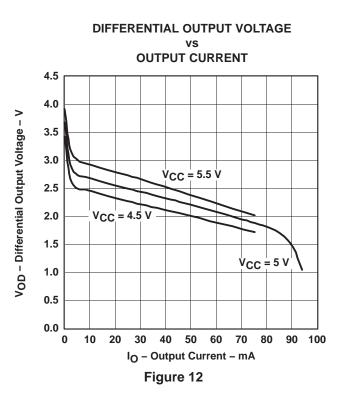
# **DRIVER DIFFERENTIAL OUTPUT VOLTAGE** FREE-AIR TEMPERATURE 3.0 VoD - Driver Differential Output Voltage - V $R_L = 54 \Omega$ $V_{CC} = 5.25 \text{ V}$ 2.5 $V_{CC} = 5 V$ 2.0 V<sub>CC</sub> = 4.75 V 1.5 1.0 20 80 -40 -20 40 60

 $T_A$  – Free-Air Temperature –  $^{\circ}C$ 

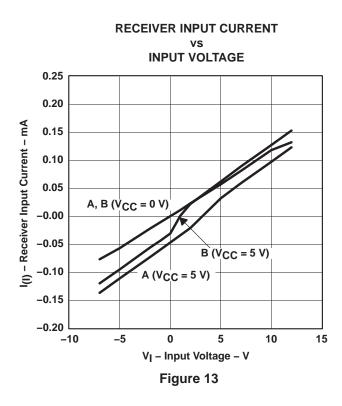
Figure 9







# TYPICAL CHARACTERISTICS



# SN65LBC184 SN75LBC184 SN75LBC184 SN75LBC184 SN75LBC184 SN75LBC184 SN75LBC184

NOTE A: The line should be terminated at both ends in its characteristic impedance (R<sub>T</sub> = Z<sub>O</sub>). Stub lengths off the main line should be kept as short as possible.

Figure 14. Typical Application Circuit



### APPLICATION INFORMATION

# 'LBC184 test description

The 'LBC184 is tested against the IEC 61000–4–5 recommended transient identified as the combination wave. The combination wave provides a 1.2-/50- $\mu$ s open-circuit voltage waveform and a 8-/20- $\mu$ s short-circuit current waveform shown in Figure 15. The testing is performed with a combination/hybrid pulse generator with an effective output impedance of 2  $\Omega$ . The setup for the overvoltage stress is shown in Figure 16 with all testing performed with power applied to the 'LBC184 circuit.

# **NOTE**High voltage transient testing is done on a sampling basis.

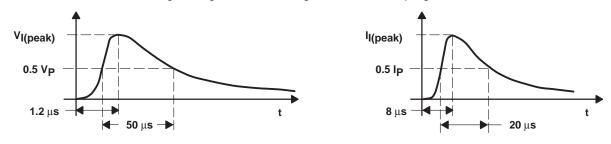


Figure 15. Short-Circuit Current Waveforms

The 'LBC184 is tested and evaluated for both maximum (single pulse) as well as life test (multiple pulse) capabilities. The 'LBC184 is evaluated against transients of both positive and negative polarity and all testing is performed with the worst-case transient polarity. Transient pulses are applied to the bus pins (A & B) across ground as shown in Figure 16.

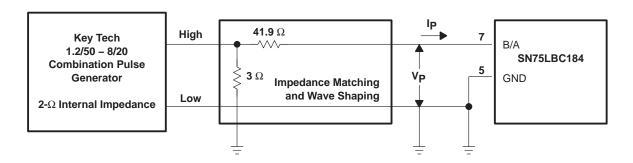


Figure 16. Overvoltage-Stress Test Circuit

An example waveform as seen by the 'LBC184 is shown in Figure 17. The bottom trace is current, the middle trace shows the clamping voltage of the device and the top trace is power as calculated from the voltage and current waveforms. This example shows a peak clamping voltage of 33.6 V and peak current of 16 A, thus yielding an absorbed peak power of 538 W.

### **NOTE**

A circuit reset may be required to ensure normal data communications following a transient noise pulse of greater than  $250~\mathrm{W}$  peak.



# **APPLICATION INFORMATION**

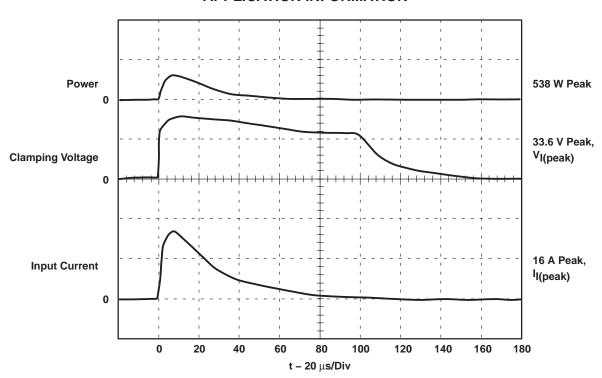


Figure 17. Typical Surge Waveform Measured At Terminals 5 and 7



## PACKAGE OPTION ADDENDUM



ti.com 12-Feb-2009

### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65LBC184D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC184DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC184DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC184DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC184P	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN65LBC184PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75LBC184D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC184DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC184DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC184DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC184P	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75LBC184PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND**: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.



# **PACKAGE OPTION ADDENDUM**

12-Feb-2009

In no event shall TI's liability arising out of such information exceed the total purchase price to Customer on an annual basis.	of the TI part(s) at issue in this document sold by T
to Customer on an annual basis.	



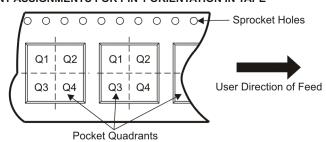
# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

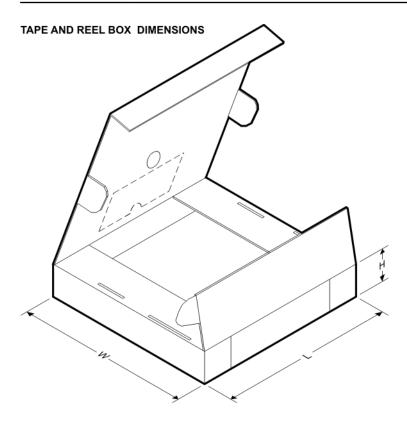
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LBC184DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75LBC184DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1





\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LBC184DR	SOIC	D	8	2500	340.5	338.1	20.6
SN75LBC184DR	SOIC	D	8	2500	340.5	338.1	20.6

# P (R-PDIP-T8)

# PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



# D (R-PDSO-G8)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



# D (R-PDSO-G8)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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